

AMENDMENTS TO THE CLAIMS

1. (Previously Presented) A method comprising:
forming a first conductive material in an opening through a dielectric to a contact point; and
forming a second conductive material on the first conductive material,
wherein the first conductive material comprises a unidirectional electrical conductivity and the unidirectional conductivity is configured to be in a direction corresponding to a projection to or from the contact point and the second conductive material.
2. (Original) The method of claim 1, wherein forming the second conductive material comprises introducing a seed material into the via in a manner that leaves the first conductive material overlying the contact point.
3. (Original) The method of claim 1, wherein the contact point is a contact point to a circuit device, and wherein forming a first conductive material includes forming in a via of the dielectric to contact the circuit device.
4. (Original) The method of claim 1, further comprising forming an interconnect structure in the opening on the second conductive material.
5. (Original) The method of claim 4, further comprising:
forming a third conductive material on an exposed portion of the interconnect structure,
wherein the third conductive material comprises a unidirectional electrical conductivity in a direction normal to the exposed portion of the interconnect structure.
6. (Currently Amended) The method of claim 6.5, further comprising:
prior to forming the third conductive material, modifying the exposed surface of the interconnect structure, wherein modifying the surface of the interconnect structure comprises one of stripping with a stripping agent, planarizing, polishing, and doping with a dopant.

7. (Original) The method of claim 1, wherein forming the first conductive material comprises deposition via one of electroplating, chemical vapor deposition, sputter deposition, molecular beam deposition, and gel separation in an electronic field.
8. (Original) The method of claim 1, wherein forming the second conductive material comprises sputter depositing the second conductive material into the opening.
9. (Original) The method of claim 1, wherein the first conductive material comprises one of an organic material, an organo-metallic material, barium, copper, a doped polymer material, and a polymer based material.
10. (Original) The method of claim 1, wherein forming the first conductive material includes forming a layer of material comprising a property tending to reduce metal diffusion between the second conductive material and the dielectric.
11. (Original) The method of claim 1, wherein forming the first conductive material includes forming a layer of material comprising a property tending to reduce electron migration between the second conductive material and the dielectric.
12. (Original) The method of claim 1, wherein forming the first conductive material includes forming a layer of material comprising a property tending to act as an etch stop layer.
13. (Original) The method of claim 1, further comprising chemically-mechanically polishing the first conductive material with a polishing slurry.
14. (Original) The method of claim 1, further comprising doping the first conductive material.

Claims 15 - 26 (Cancelled)